

Number	Date	Location	IP	Time Stamp
1	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:04
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
2	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:07
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
3	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:11
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
931	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:11
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
932	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:11
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
46	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:11
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
9	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:11
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
190	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:29
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
10	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:30
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
4	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:53
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
158	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 15:10
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
6	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:58
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
8	2003/03/14	near10 (passivation)	USIAT;	2003/03/14 14:58
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	
			USIAT;	2003/03/14 15:11
			US-PGPUB;	
			EPG; JPC;	
			DERWENT;	
			IBM_TDB	

-	31	source and drain adj electrode nearl0 semiconductor adj layer	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	7	semiconductor adj layer nearl0 gate adj insulating nearl0 active nearl0 gate adj electrode and source and drain adj electrode nearl0 semiconductor adj layer	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	101	drain adj electrode nearl0 reduced nearl0 side of area	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	4	contact adj hole nearl0 edge of side nearl0 drain adj electrode and drain adj electrode nearl0 reduced nearl0 side of area	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	81	contact adj hole nearl0 drain adj electrode nearl0 pixel adj region	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	4	contact adj hole nearl0 over nearl0 (drain adj electrode) nearl0 over nearl0 pixel adj region	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	3767	contact adj hole nearl0 (passivation) nearl0 expos\$6 (drain adj electrode) nearl0 (insulating)	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	21	contact adj hole nearl0 (passivation) nearl0 expos\$6 nearl0 (drain adj electrode) nearl0 (insulating)	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 16:44
-	9	contact adj hole nearl0 formed nearl0 over nearl0 (drain and pixel)	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 09:50
-	1	6532050.did.	USP&T; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/15 09:50